FAIRCHILD SEMICONDUCTOR®

March 2013

FDD7N25LZ

N-Channel UniFET™ MOSFET

250 V, 6.2 A, 550 mΩ

Features

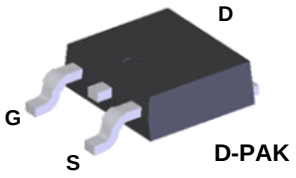
- $R_{DS(on)}$ = 430 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 3.1 A
- Low Gate Charge (Typ.12 nC)
- Low C_{rss} (Typ. 8 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

Description

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

Applications

- LCD/LED/PDP TV
- Consumer Appliances
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply



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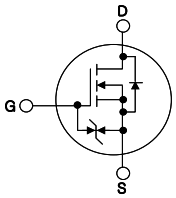


MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter			FDD7N20LZ	Unit
V_{DSS}	Drain to Source Voltage			250	V
V_{GSS}	Gate to Source Voltage			±20	V
I_D	Drain Current	- Continuous (T_C = 25°C)		6.2	A
		- Continuous (T_C = 100°C)		3.7	
I_{DM}	Drain Current	- Pulsed	(Note 1)	25	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	115	mJ
I_{AR}	Avalanche Current		(Note 1)	5.5	A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	5.6	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	10	V/ns
P_D	Power Dissipation	(T_C = 25°C)		56	W
		- Derate above 25°C		0.45	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FDD7N20LZ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	110	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD7N25LZ	FDD7N25LZ	D-PAK	380mm	16mm	2500

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, T_C = 25°C	250	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.25	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 200V, T_C = 125°C	-	-	10	
I_{GSSF}	Gate to Body Leakage Current, Forward	V_{GS} = 20V, V_{DS} = 0V	-	-	10	μA
I_{GSSR}	Gate to Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	-	-	-10	μA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.0	-	2.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 3.1A	-	0.43	0.55	Ω
		V_{GS} = 5V, I_D = 3.1A	-	0.45	0.57	
g_{FS}	Forward Transconductance	V_{DS} = 20V, I_D = 3.1A	-	7	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V f = 1MHz	-	480	635	pF
C_{oss}	Output Capacitance		-	65	85	pF
C_{rss}	Reverse Transfer Capacitance		-	8	12	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 250V I_D = 6.2A V_{GS} = 10V (Note 4)	-	12	16	nC
Q_{gs}	Gate to Source Gate Charge		-	1.5	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 250V, I_D = 6.2A V_{GS} = 10V, R_G = 25Ω (Note 4)	-	10	30	ns
t_r	Turn-On Rise Time		-	15	40	ns
$t_{d(off)}$	Turn-Off Delay Time		-	75	160	ns
t_f	Turn-Off Fall Time		-	30	70	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 6.2A	-	-	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 6.2A dI_F/dt = 100A/μs	-	130	-	ns
Q_{rr}	Reverse Recovery Charge		-	0.6	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 6mH, I_{AS} = 6.2A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 6.2A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

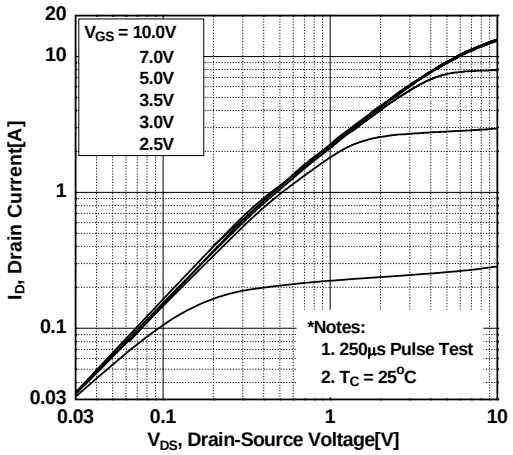


Figure 2. Transfer Characteristics

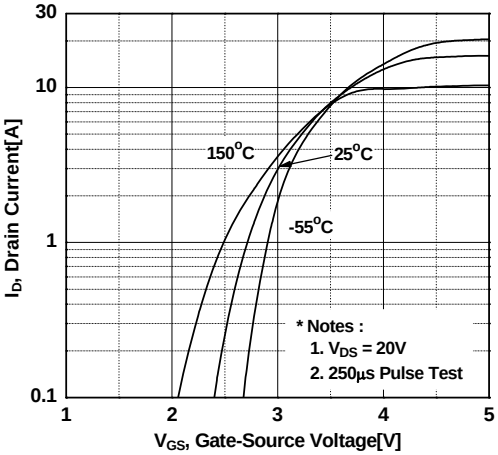


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

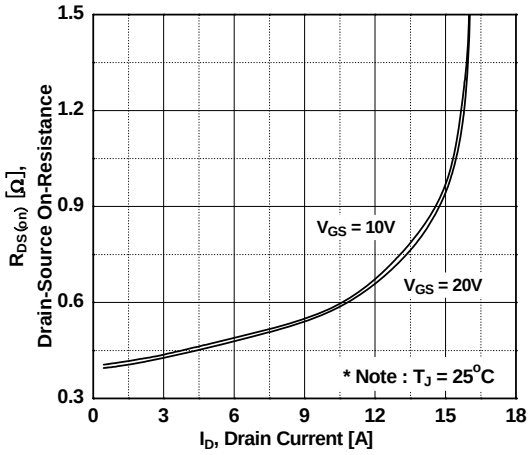


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

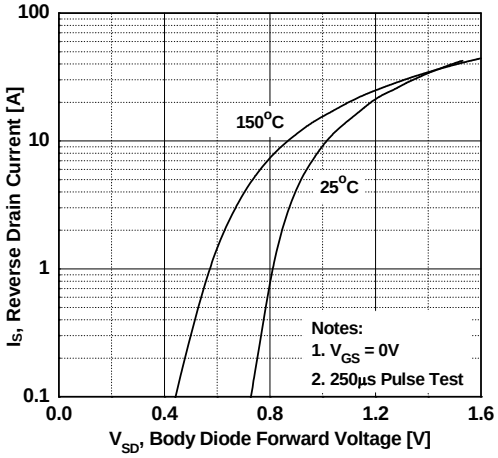


Figure 5. Capacitance Characteristics

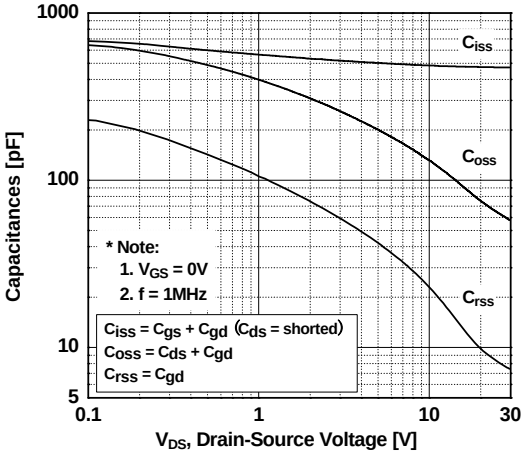
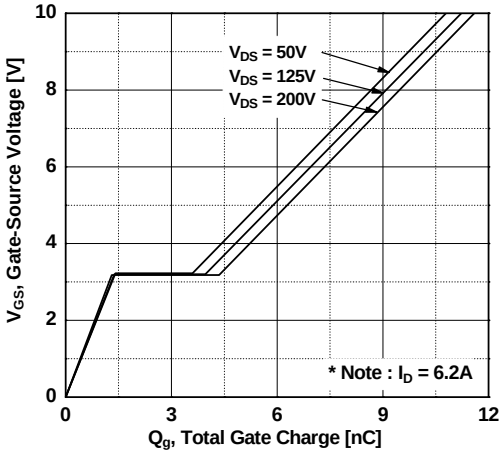


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

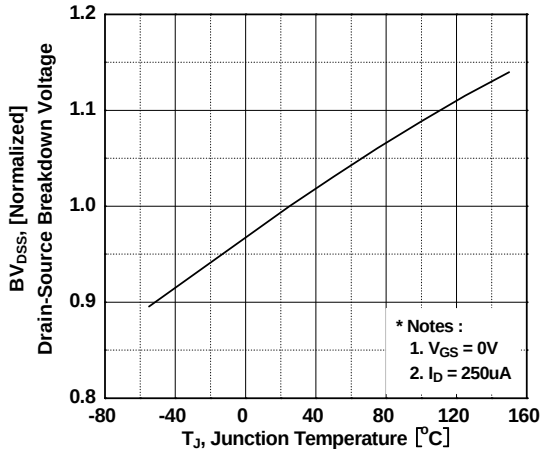


Figure 8. On-Resistance Variation vs. Temperature

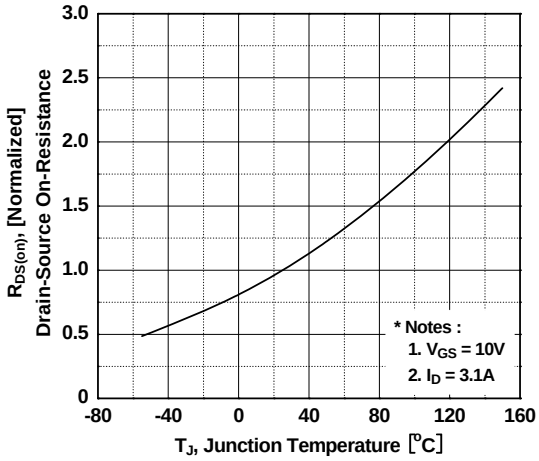


Figure 9. Maximum Safe Operating Area - FDD7N25LZ

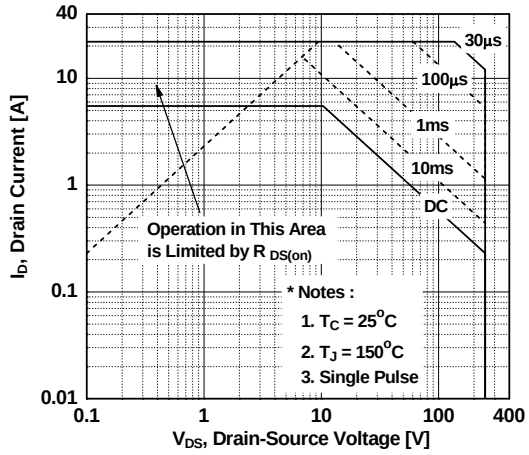


Figure 10. Maximum Drain Current vs. Case Temperature

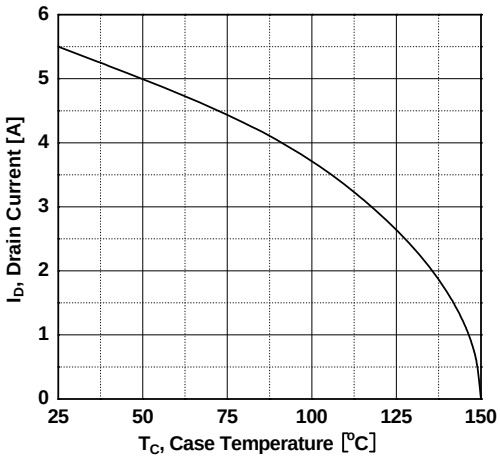
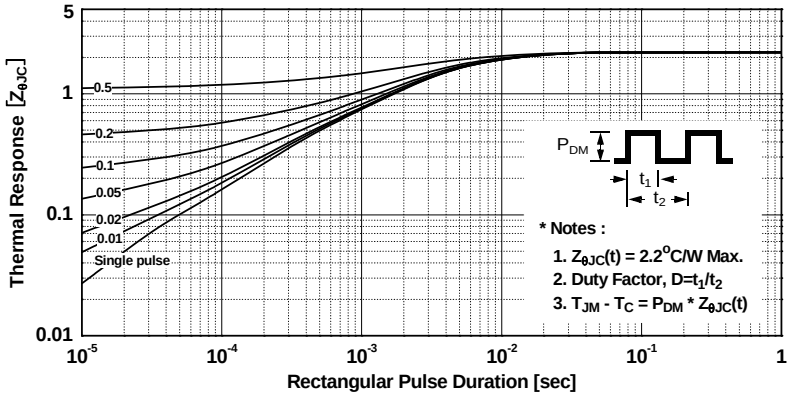
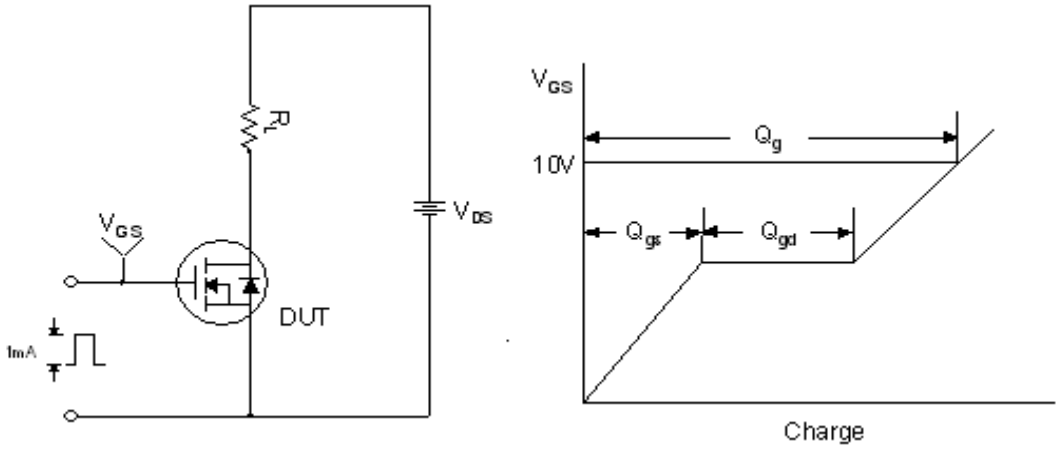


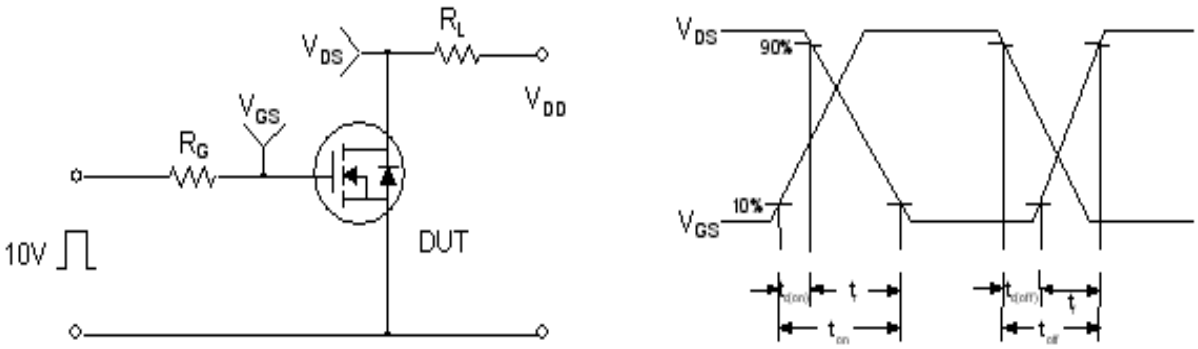
Figure 11. Transient Thermal Response Curve - FDD7N25LZ



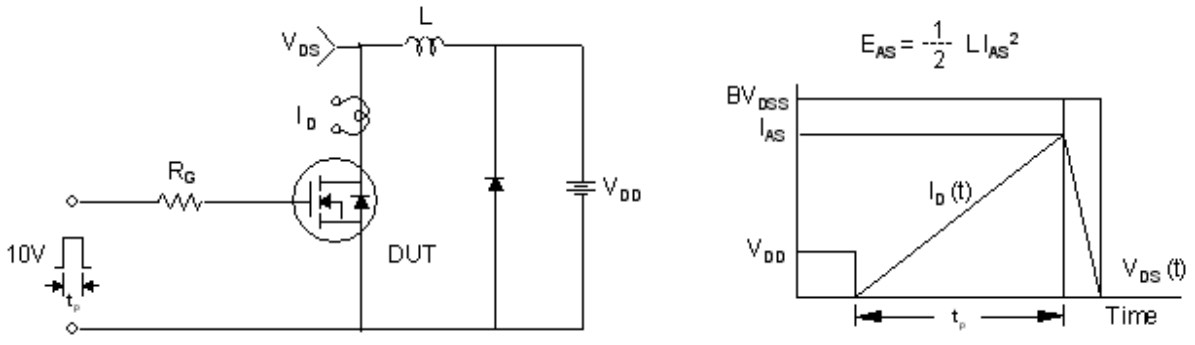
Gate Charge Test Circuit & Waveform



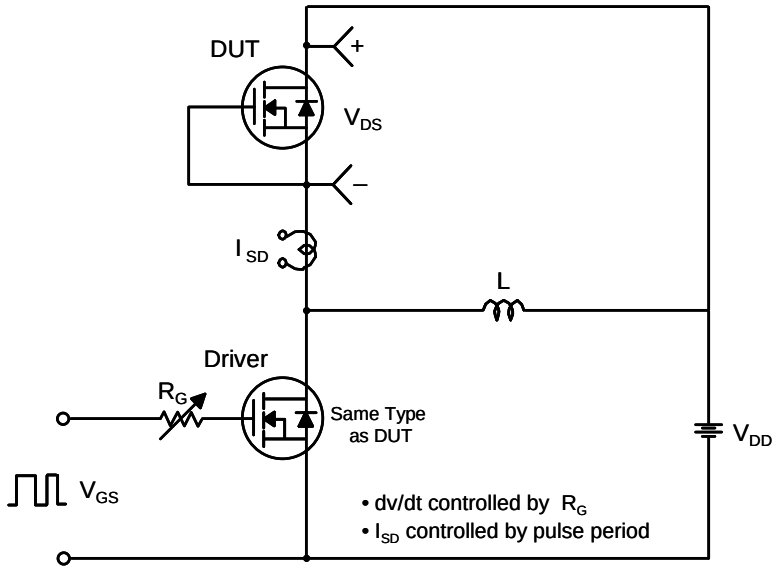
Resistive Switching Test Circuit & Waveforms

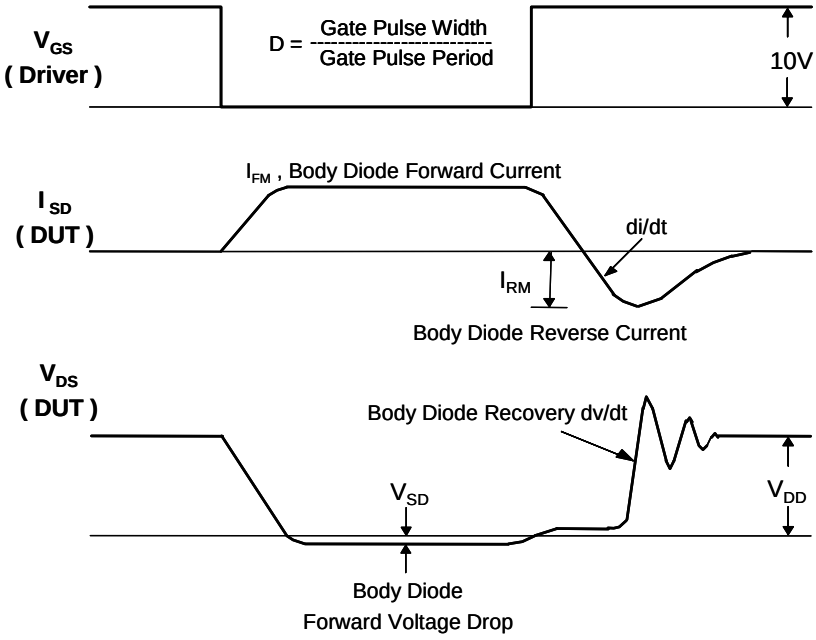


Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

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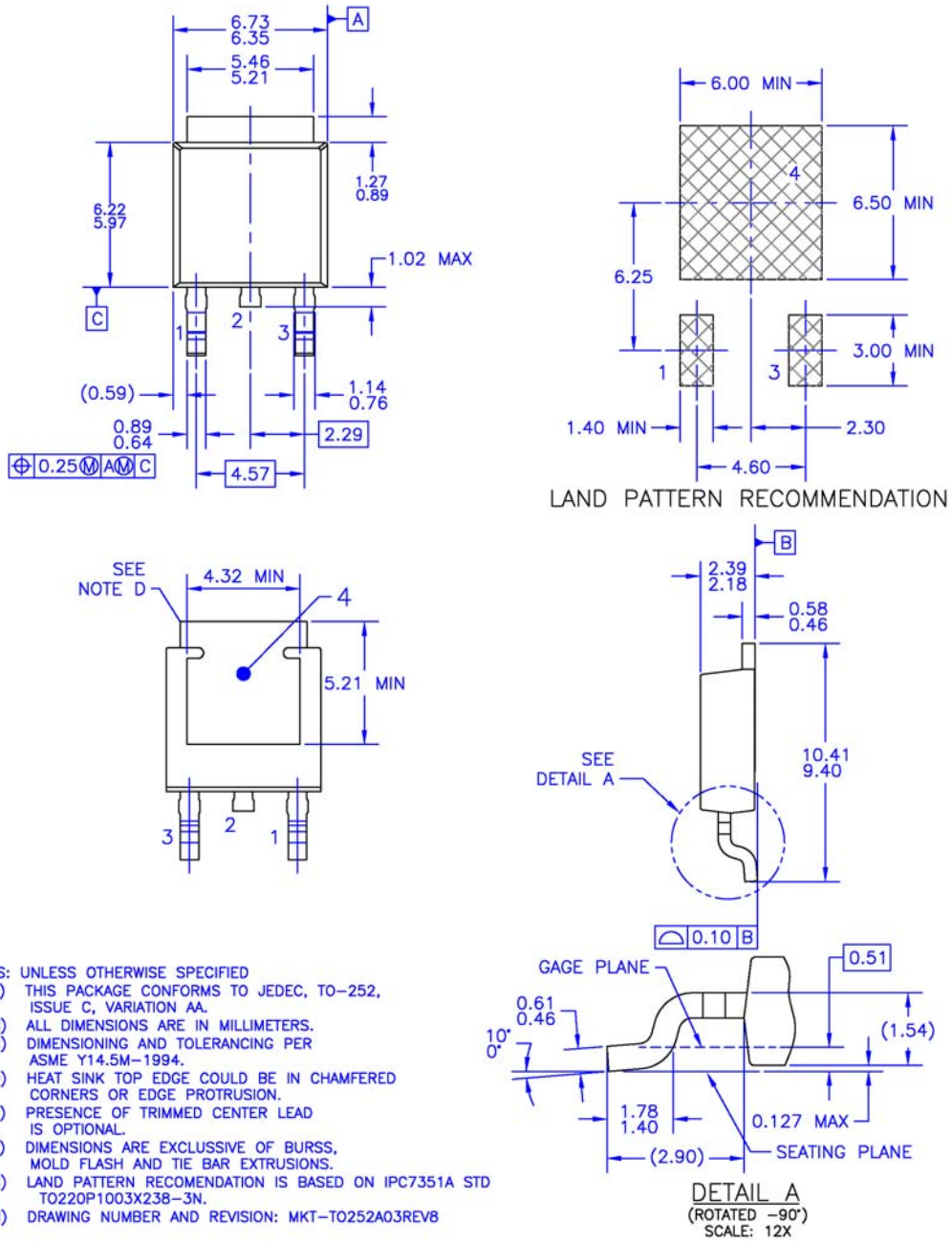

NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO−252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M−1994.
D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.
F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO220P1003X238−3N.
H) DRAWING NUMBER AND REVISION: MKT−TO252A03REV8

Dimensions in Millimeters

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